

650 V, 33 mOhm Gallium Nitride (GaN) FET in a CCPAK1212i package 19 April 2021

**Objective data sheet** 

### 1. General description

The GAN039-650NTB is a 650 V, 33 mΩ Gallium Nitride (GaN) FET in a CCPAK1212i inverted package. It is a normally-off device that combines Nexperia's latest high-voltage GaN HEMT H2 technology and low-voltage silicon MOSFET technologies — offering superior reliability and performance.

### 2. Features and benefits

- Simplified driver design as standard level MOSFET gate drivers can be used:
  - 0 V to 12 V drive voltage
  - Gate threshold voltage V<sub>GSth</sub> of 4 V
- Robust gate oxide with ±20 V V<sub>GS</sub> rating
- High gate threshold voltage of 4 V for gate bounce immunity
- Low body diode V<sub>f</sub> for reduced losses and simplified dead-time adjustments
- Transient over-voltage capability for increased robustness
- CCPAK package technology:
  - Improved reliability, with reduced  $\mathsf{R}_{\mathsf{th}(j\mathsf{-}\mathsf{mb})}$  for optimal cooling
  - Lower inductances for lower switching losses and EMI
  - 175 °C maximum junction temperature
  - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
  - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joints

### 3. Applications

- Hard and soft switching converters for industrial and datacom power
- Bridgeless totempole PFC
- PV and UPS inverters
- Servo motor drives

### 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	-55 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	650	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C	-	-	60	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	300	W
Tj	junction temperature		-55	-	175	°C
Static chara	octeristics			_		
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 32 A; T <sub>j</sub> = 25 °C	-	33	39	mΩ



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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cha	aracteristics	· · · · · · · · · · · · · · · · · · ·	·			
Q <sub>GD</sub>	gate-drain charge	$I_D$ = 32 A; $V_{DS}$ = 400 V; $V_{GS}$ = 10 V;	-	5	-	nC
Q <sub>G(tot)</sub>	total gate charge	T <sub>j</sub> = 25 °C	-	30	-	nC
Source-drain	n diode		· · · · ·			
Q <sub>r</sub>	recovered charge	$I_{S} = 32 \text{ A}; \text{ dI}_{S}/\text{dt} = -1000 \text{ A}/\mu\text{s};$ $V_{GS} = 0 \text{ V}; V_{DS} = 400 \text{ V}; \frac{\text{Fig. 3}}{2}$	-	150	-	nC

# 5. Pinning information

Table 2	2. Pinning info			1
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	6 5 4 3 2 1	D
2	S	source		
3	S	source		
4	S	source		
5	S	source		
6	S	source		
7	D	drain	CCPAK (SOT8005)	
8	D	drain		aaa-028116
9	D	drain		
10	D	drain		
11	D	drain		
12	D	drain	1	
mb	S	mounting base; connected to source		

# 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
GAN039-650NTB	ССРАК	Plastic, surface mounted copper clip package inverted (CCPAK1212i); 13 terminals; 2.0 mm pitch, 12 mm x 12 mm x 2.5 mm body	SOT8005			

### 7. Marking

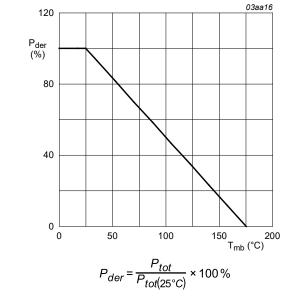
Table 4. Marking codes						
Type number	Marking code					
GAN039-650NTB	039INTBX					

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	-55 °C ≤ T <sub>j</sub> ≤ 175 °C	-	650	V
V <sub>TDS</sub>	transient drain to source voltage	pulsed; $t_p = 1 \ \mu s$ ; $\delta_{factor} = 0.01$	-	[tbd]	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	300	W
ID	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C	-	60	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C	-	42	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>mb</sub> = 25 °C	-	240	А
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-drai	n diode				
Is	source current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 0 V	-	55	А
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>mb</sub> = 25 °C	-	240	A





### 9. Thermal characteristics

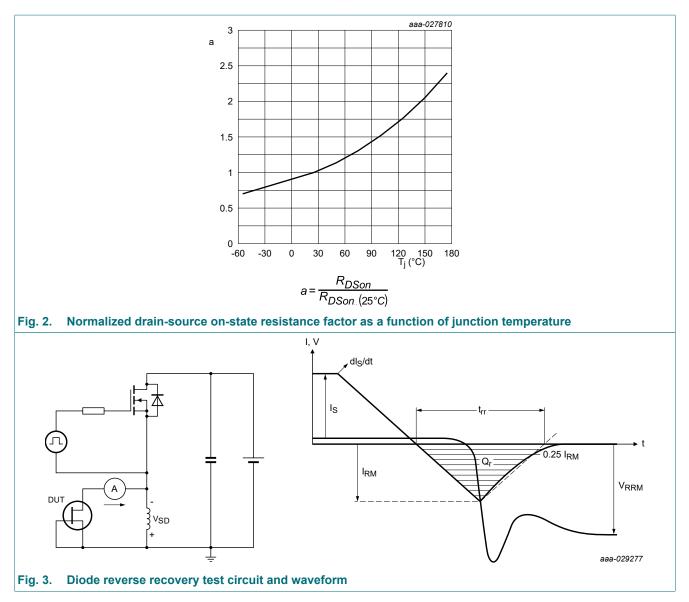
Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	0.5	K/W

GAN039-650NTB

### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara		Conditions		אני	Max	onn
					1.0	
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	3.3	4	4.8	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 650 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	[tbd]	[tbd]	μA
		V <sub>DS</sub> = 650 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	[tbd]	-	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	10	400	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	10	400	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 32 A; T <sub>j</sub> = 25 °C	-	33	39	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 32 A; T <sub>j</sub> = 175 °C; Fig. 2	-	80	-	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.88	-	Ω
Dynamic ch	naracteristics	· ·	I			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 32 A; V <sub>DS</sub> = 400 V; V <sub>GS</sub> = 10 V;	-	30	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	9	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	5	-	nC
C <sub>iss</sub>	input capacitance	$\label{eq:VDS} \begin{array}{c} V_{DS} = 400 \; V; \; V_{GS} = 0 \; V; \; f = 1 \; MHz; \\ T_{j} = 25 \; ^{\circ}C \end{array}$	-	1500	-	pF
C <sub>oss</sub>	output capacitance		-	147	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	5	-	pF
C <sub>o(er)</sub>	effective output capacitance, energy related	$0 V \le V_{DS} \le 400 V; V_{GS} = 0 V;$ f = 1 MHz; T <sub>j</sub> = 25 °C	-	220	-	pF
C <sub>o(tr)</sub>	effective output capacitance, time related		-	380	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 400 V; R <sub>L</sub> = 12.5 Ω; V <sub>GS</sub> = 12 V;	-	[tbd]	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 30 \Omega$	-	[tbd]	-	ns
t <sub>d(off)</sub>	turn-off delay time	1 – – – – – – – – – – – – – – – – – – –	-	[tbd]	-	ns
t <sub>f</sub>	fall time	1	-	[tbd]	-	ns
Q <sub>oss</sub>	output charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 400 V	-	150	-	nC
Source-drai	in diode	· ·				
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 32 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	1.8	-	V
		$I_{S} = 16 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	1.3	-	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 32 A; dI <sub>S</sub> /dt = -1000 A/µs;	-	[tbd]	-	ns
Qr	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 400 V; <u>Fig. 3</u>	-	150	-	nC

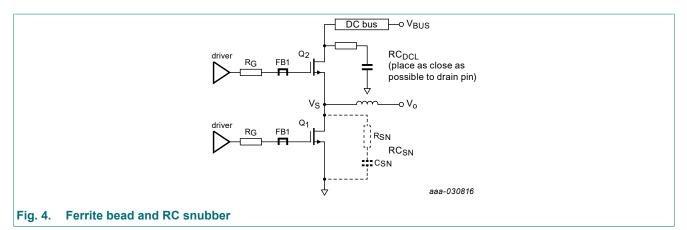
#### 650 V, 33 mOhm Gallium Nitride (GaN) FET in a CCPAK1212i package



### **11. Application information**

A Ferrite bead must be fitted in series with the gate of the GaN FET and should be located as close as possible to the gate pin, (see figure below). Keeping the gate-source loop as compact as possible minimizes the gate loop inductance. The Ferrite bead damps the resonant circuit made up of the gate source loop inductance and the GaN FET input capacitance, thus providing fast switching stability. It is recommended that the impedance of the ferrite bead should be 30  $\Omega$  @ 100 MHz, (recommended p/n BLM18PG300SN1D). A series resistance (R<sub>G</sub>) of 10 - 15  $\Omega$  is also recommended.

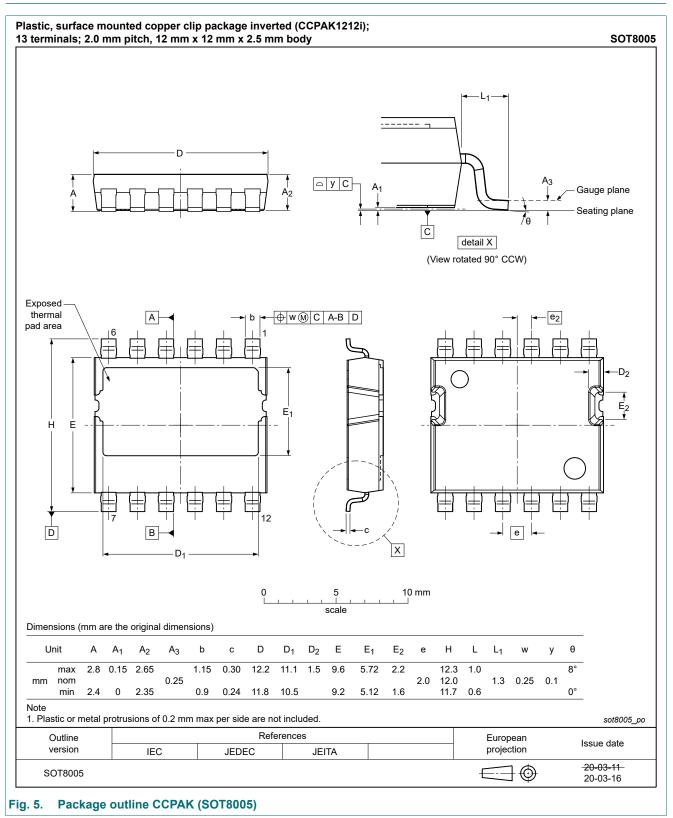
#### 650 V, 33 mOhm Gallium Nitride (GaN) FET in a CCPAK1212i package



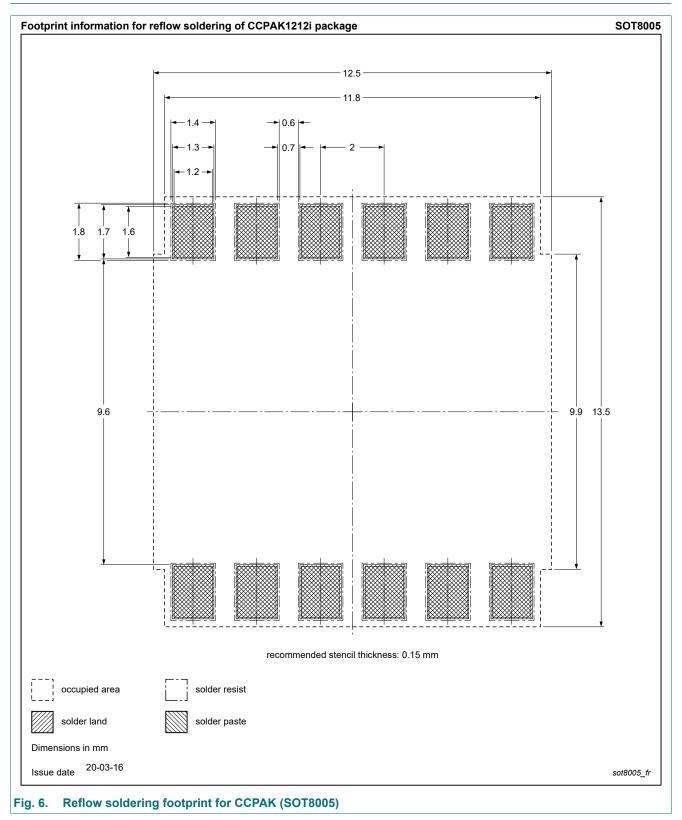
A DC-link snubber is recommended in all cases. Optimal is 20 nF in series with 4  $\Omega$ , most easily achieved with parallel combination 10 nF and 8  $\Omega$ . This snubber lowers the Q factor of any resonance in the bus. That resonance will act as a load on the high gain amplifier that is the GaN FET and can lead to instability.

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# 12. Package outline



### 13. Soldering



### 14. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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